

FIG.1

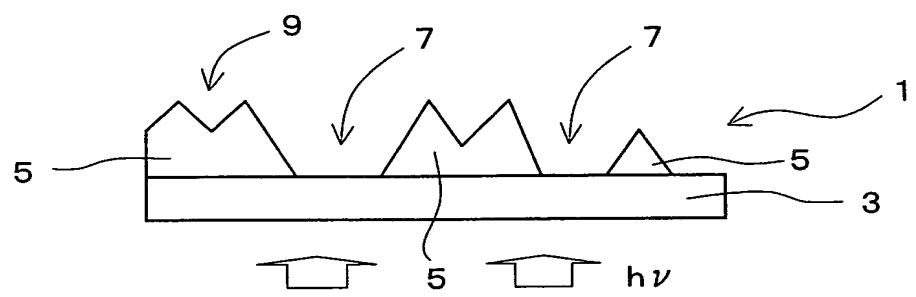


FIG.2

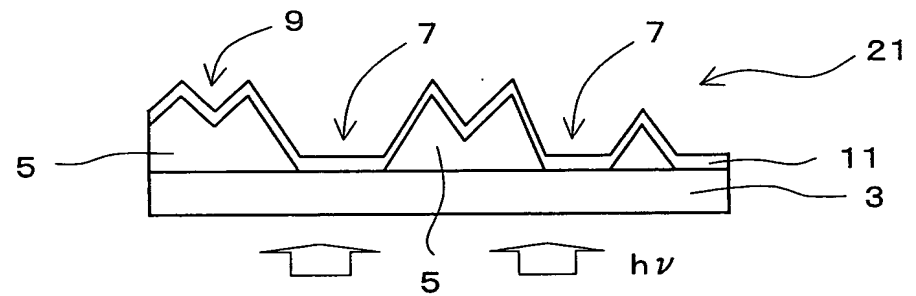


FIG.3

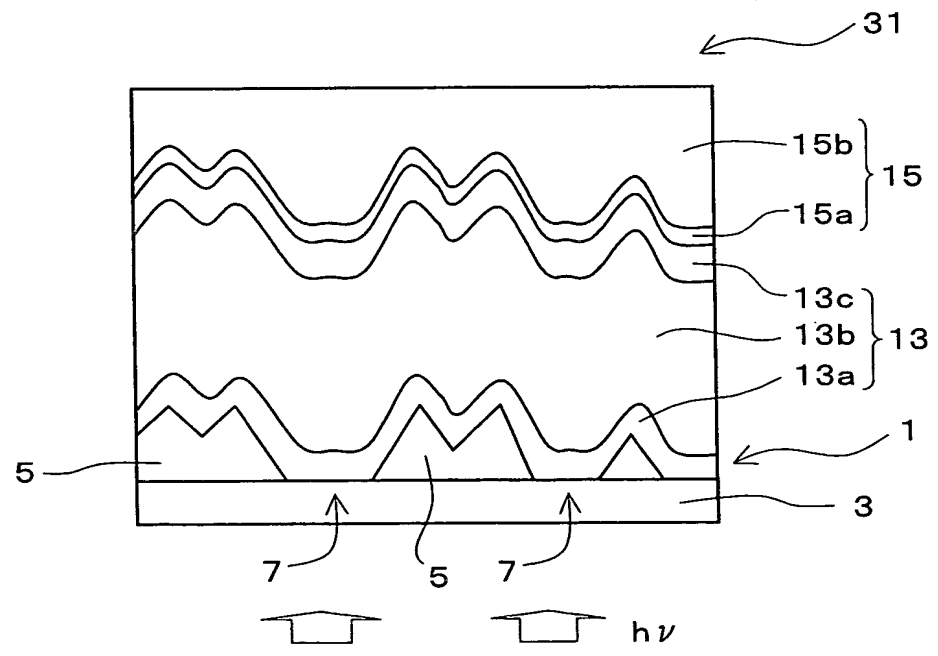


FIG.4

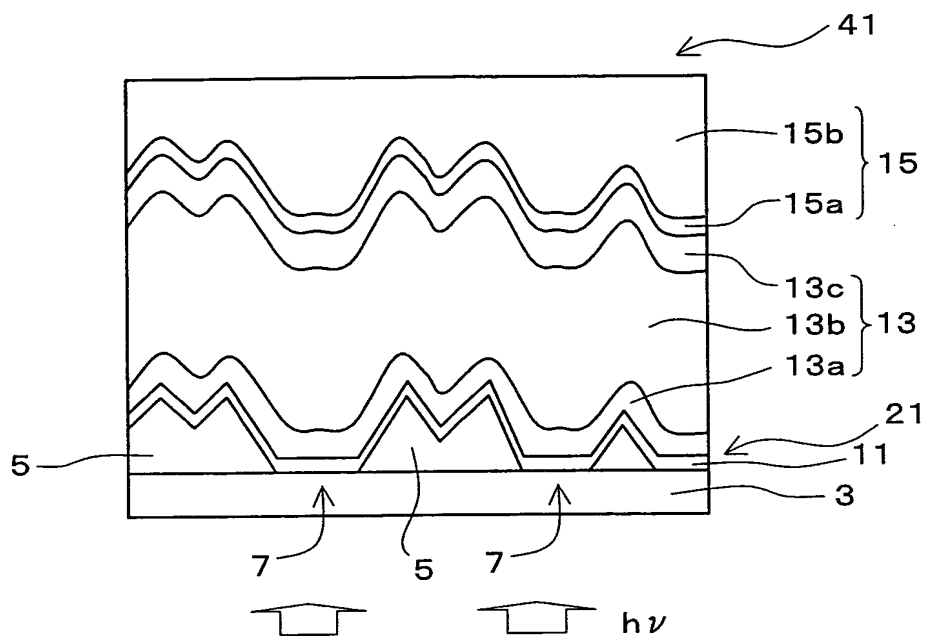


FIG.5

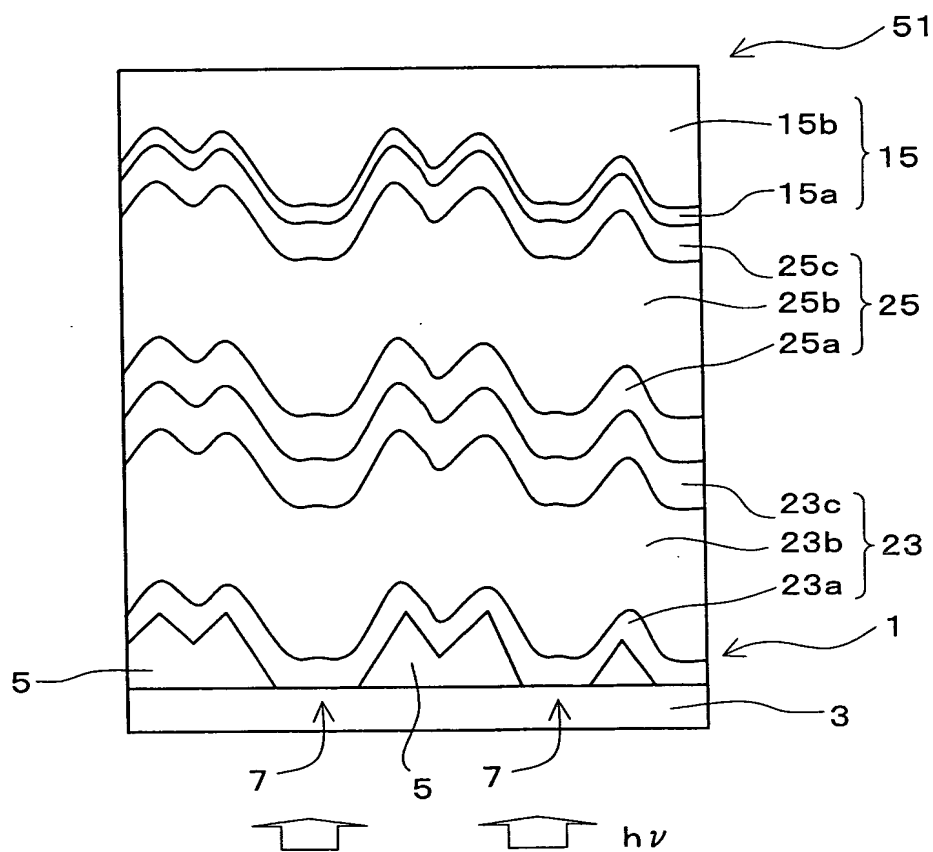


FIG.6

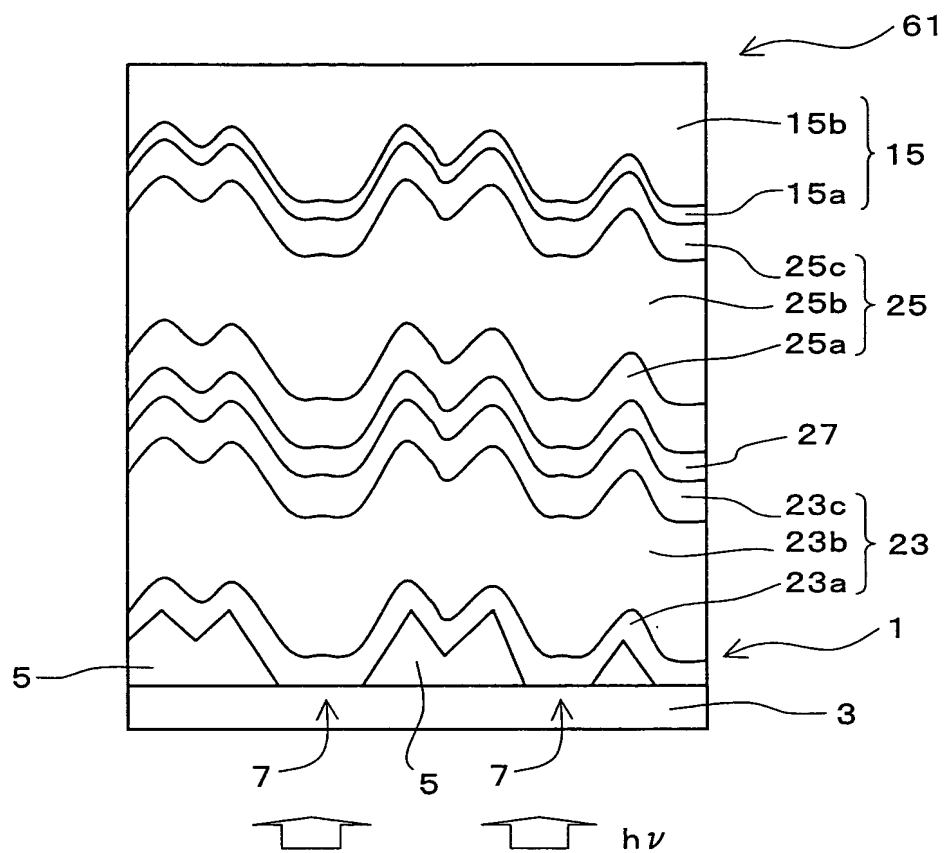


FIG.7

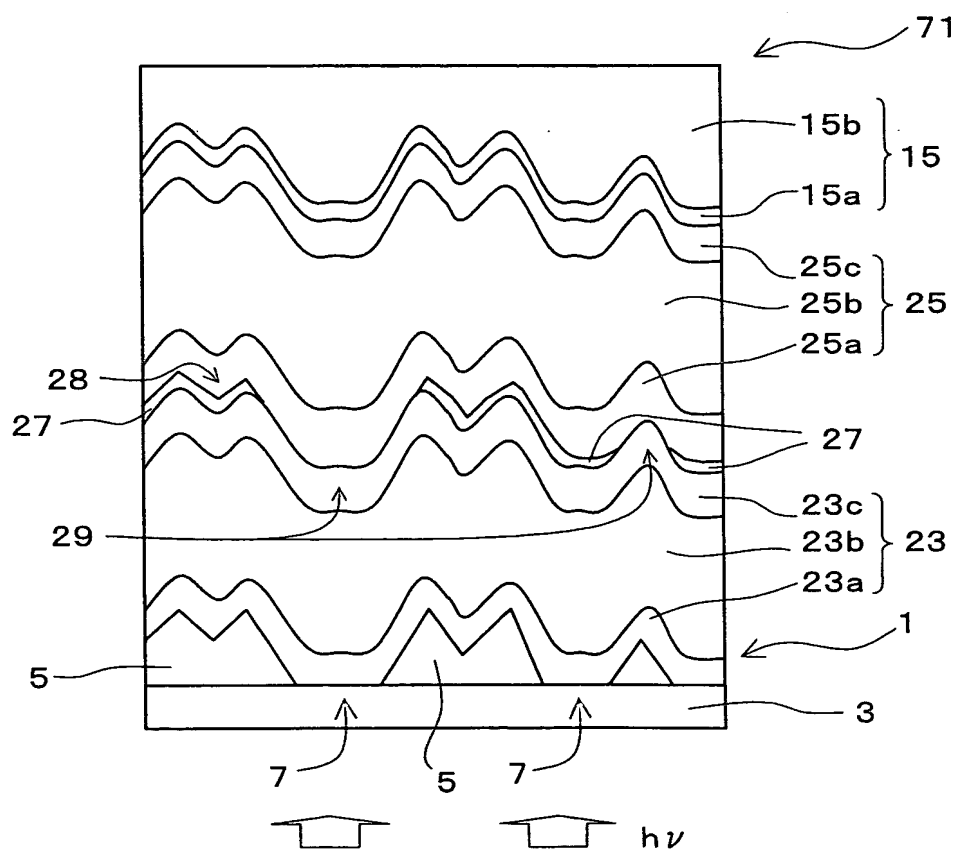


FIG.8

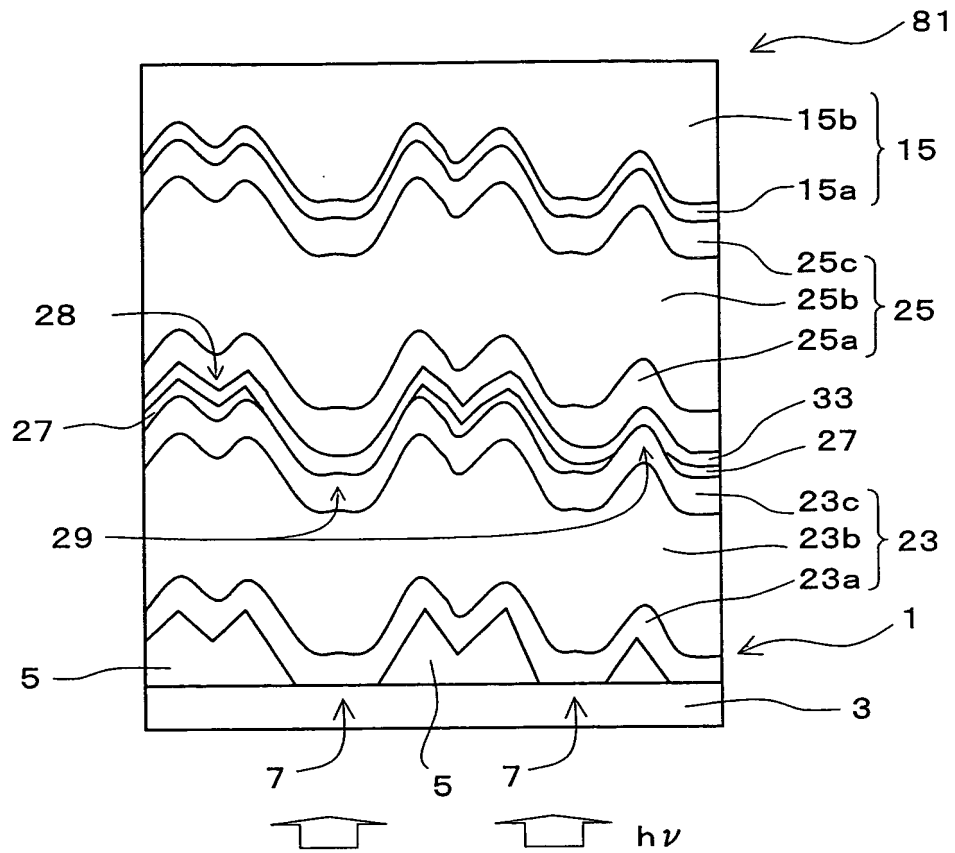
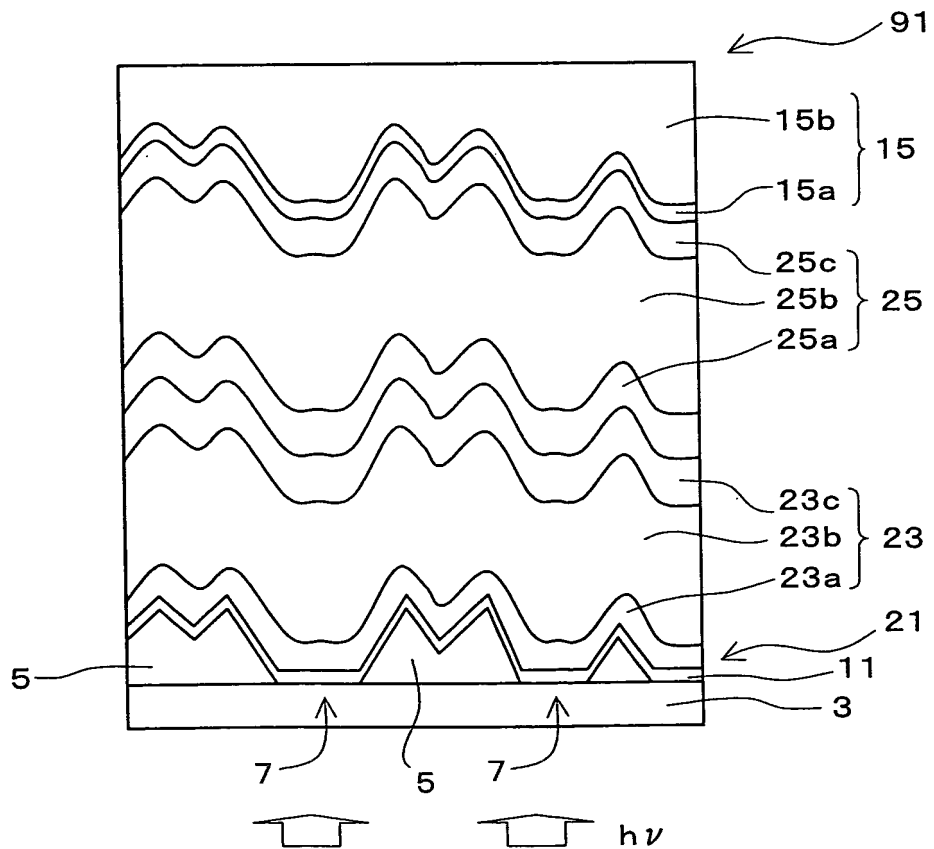


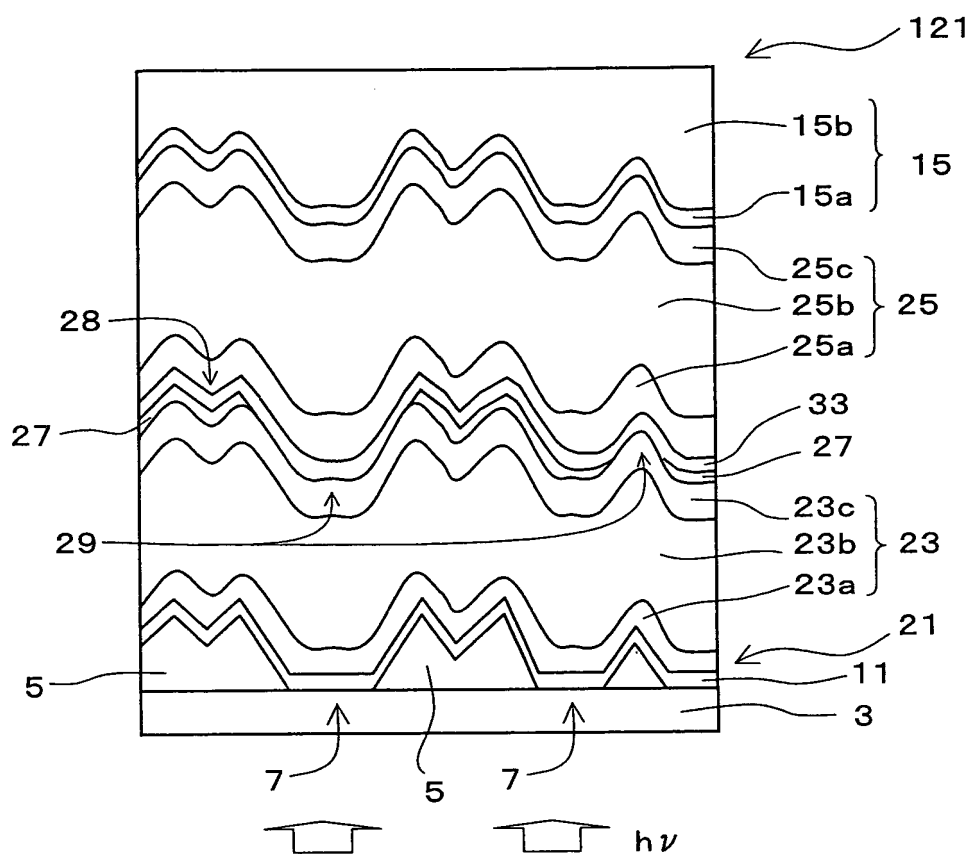
FIG.9



A cross-sectional diagram of a semiconductor device. The device consists of a substrate 3, a thin layer 11, and a patterned layer 5. Above the patterned layer 5, there are several layers of a wavy pattern. The wavy pattern is divided into four groups: 15 (layers 15a and 15b), 25 (layers 25a, 25b, and 25c), 23 (layers 23a, 23b, and 23c), and 27. A layer 21 is located between the patterned layer 5 and the wavy pattern layers. A layer 7 is located between the patterned layer 5 and the thin layer 11. A layer 101 is located above the wavy pattern layers. Arrows indicate the direction of light $h\nu$ incident on the device.

[illegible]

FIG.12



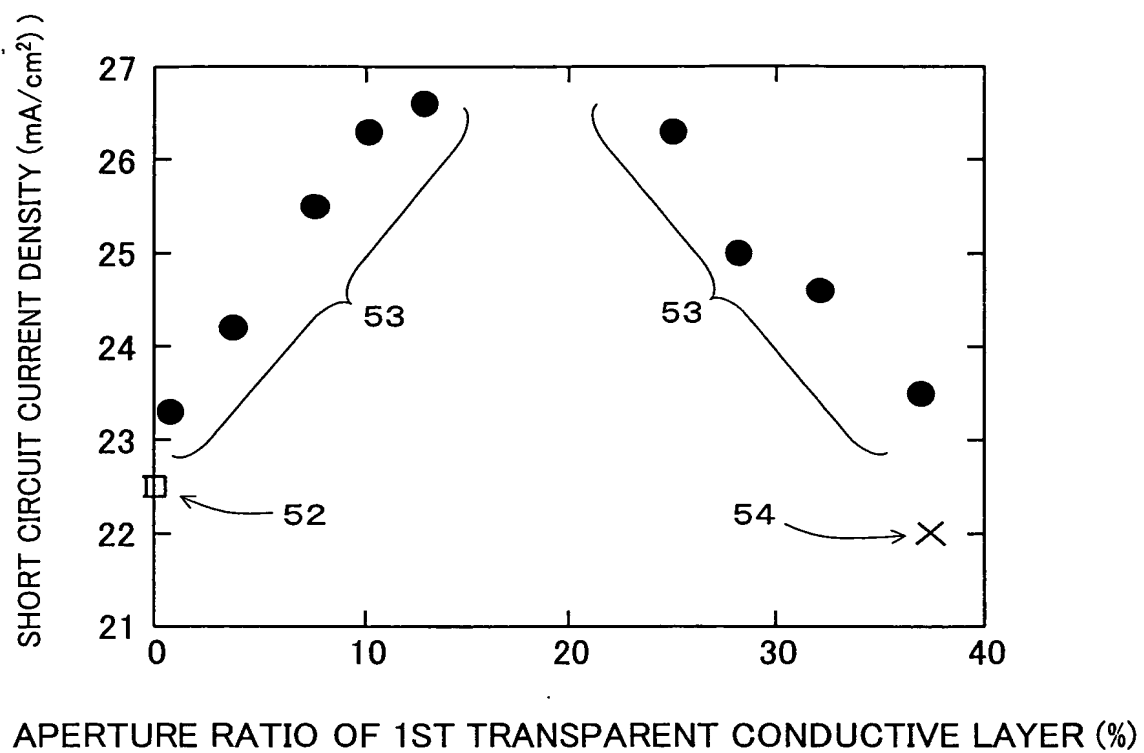


FIG.13

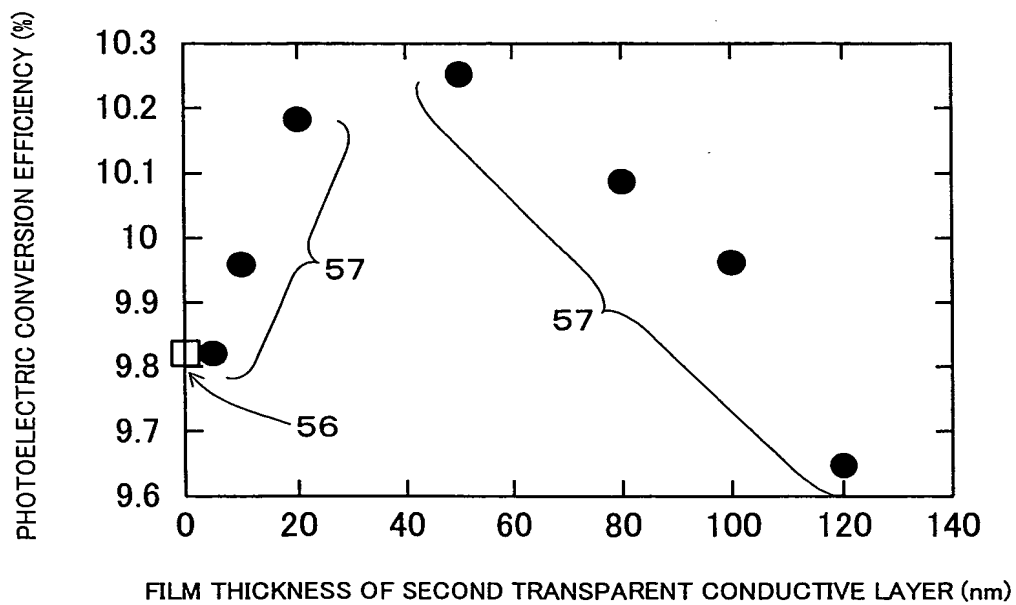


FIG.14

FIG.15

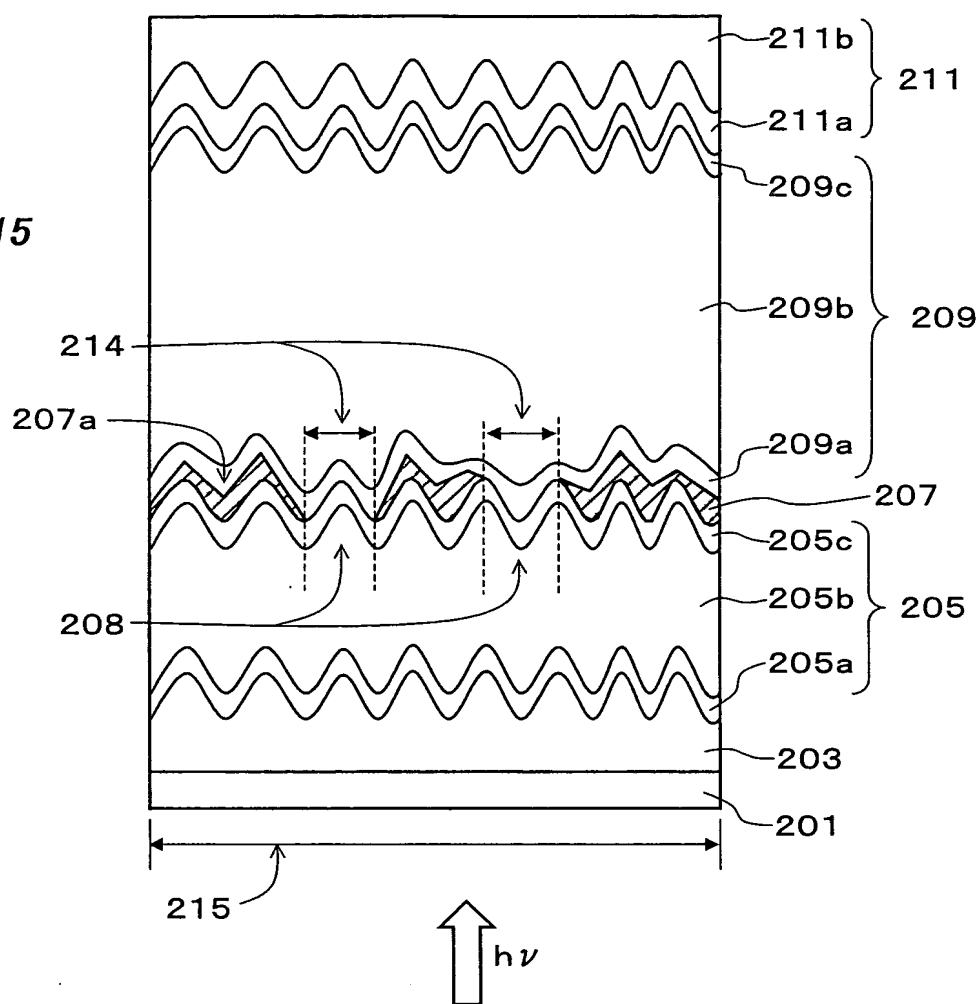


FIG.16

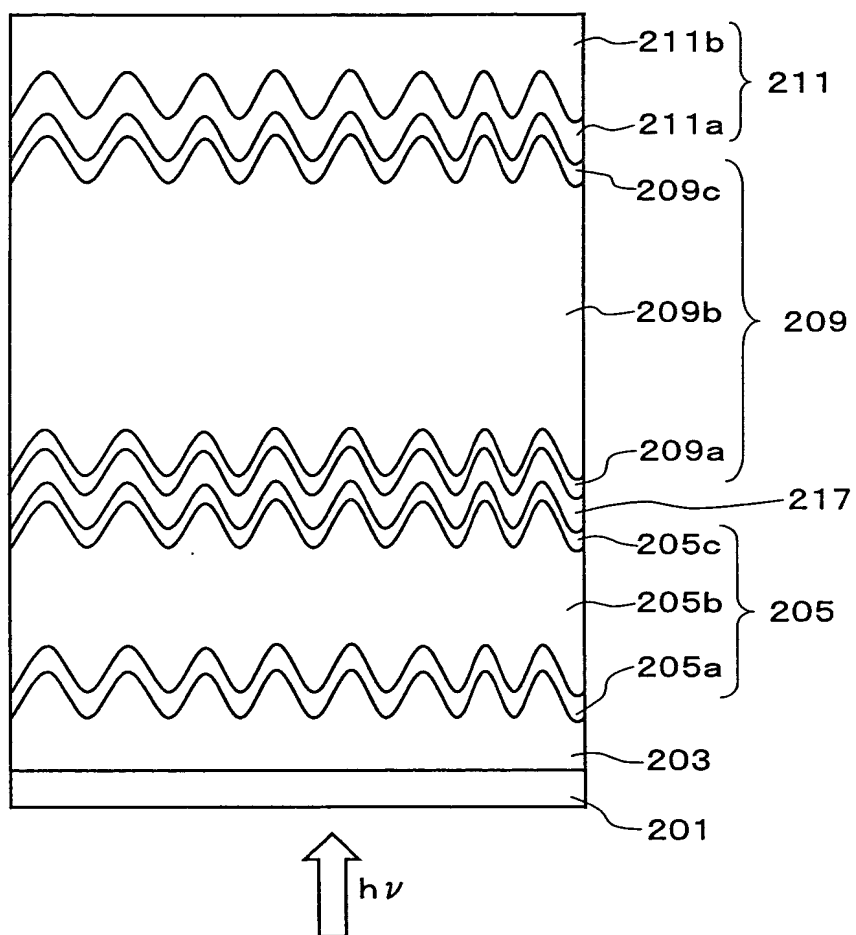
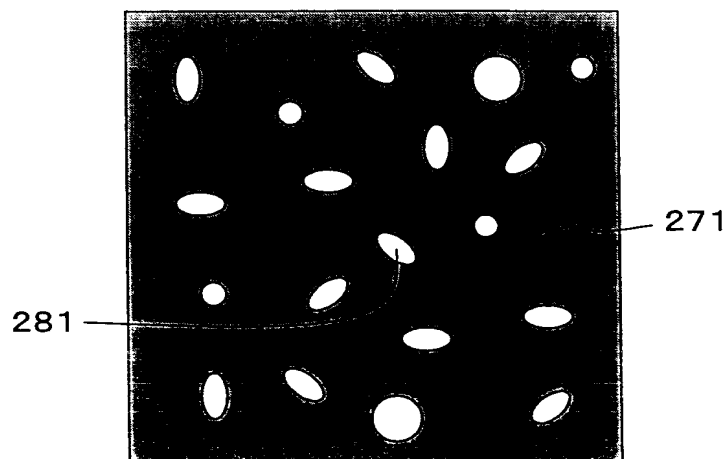


FIG.17



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FIG.18

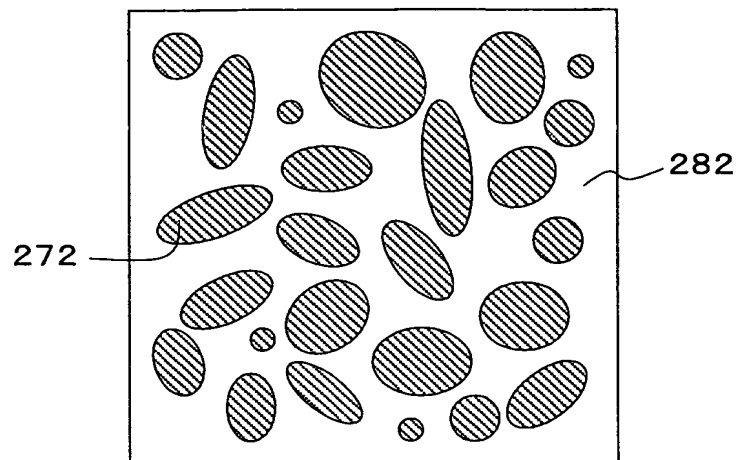
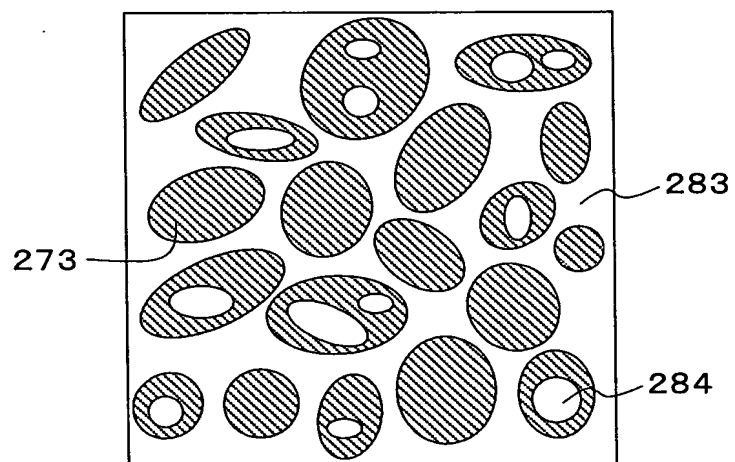


FIG.19



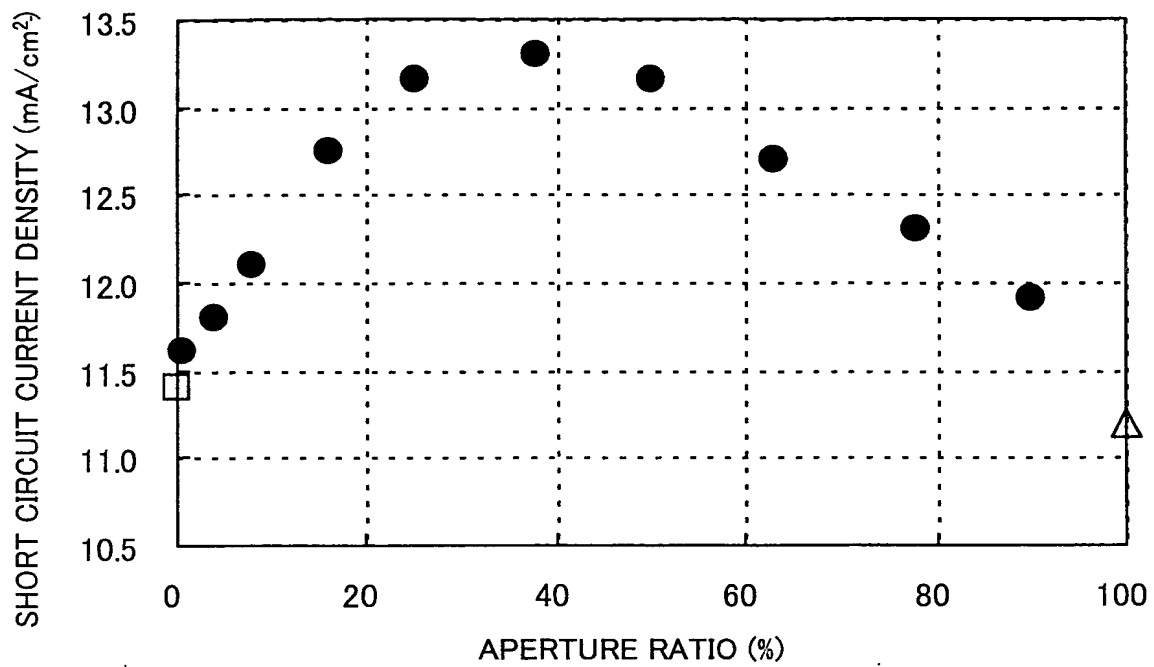


FIG.20

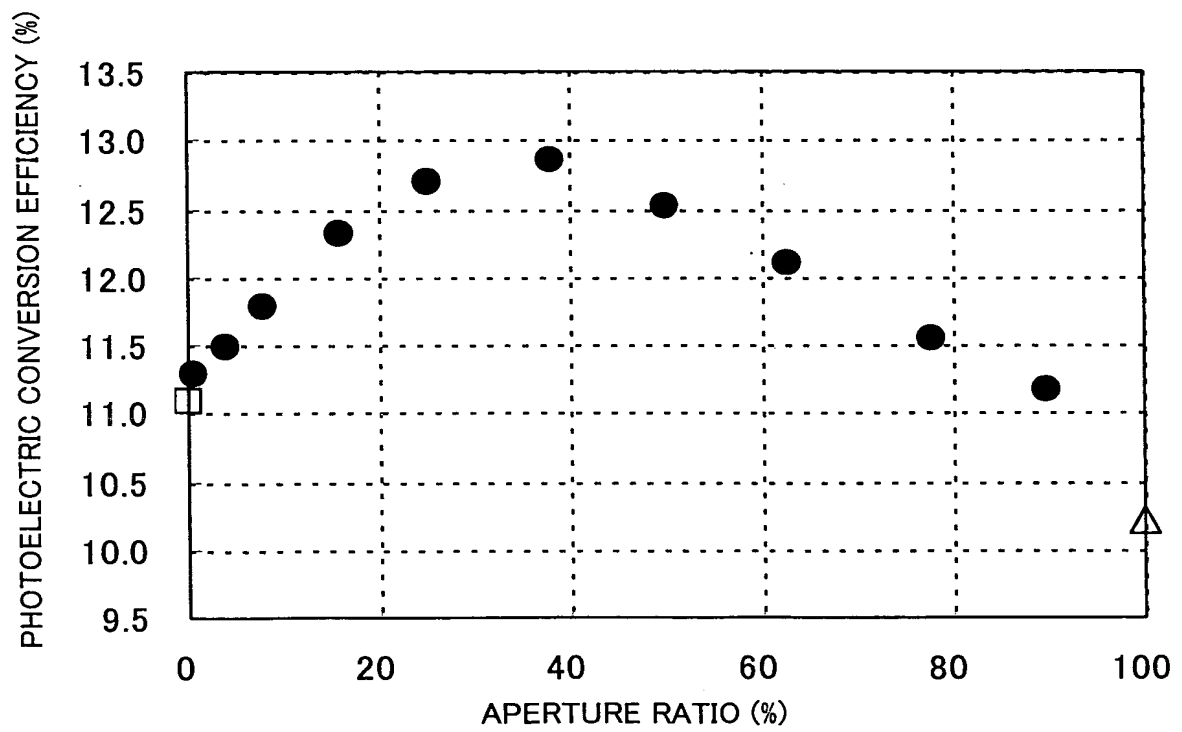


FIG.21